

# **DCR1710F18**

## **Phase Control Thyristor**

DS6028-2 June 2019 (LN38847)

### **FEATURES**

- **Double Side Cooling**
- **High Surge Capability**

**High Power Drives** 

Static Switches

**VOLTAGE RATINGS** 

Part and Ordering

Number

DCR1710F18

DCR1710F16

DCR1710F14

DCR1710F12

High Voltage Power Supplies

**Repetitive Peak** 

Voltages

 $V_{\text{DRM}}$  and  $V_{\text{RRM}}$ v

1800

1600

1400

1200

Conditions

V<sub>DSM</sub> & V<sub>RSM</sub> =

respectively

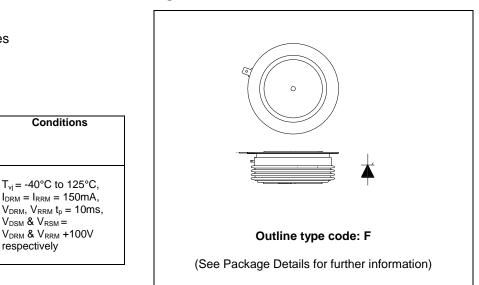
 $V_{DRM} \& V_{RRM} + 100V$ 

**APPLICATIONS** 

#### **KEY PARAMETERS**

V <sub>DRM</sub>	1800 V
I <sub>T(AV)</sub>	1710 A
I <sub>TSM</sub>	25000 A
dV/dt*	1000 V/µs
dl/dt	200 A/µs

#### \* Higher dV/dt selections available



Lower voltage grades available.

#### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR1710F18

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.





#### **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1710	А
I <sub>T(RMS)</sub>	RMS value	-	2680	А
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	2420	А

### SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	25.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	V <sub>R</sub> = 0	3.13	MA <sup>2</sup> s

### THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	5	Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.02	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.005	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-40	140	°C
Fm	Clamping force			18	26	kN

### DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ons	Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	150	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, gate open		-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2000A	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, $10\Omega$ ,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
VT	On-state voltage	I <sub>T</sub> = 1500A, T <sub>case</sub> = 125°C			1.18	V
V <sub>T(TO)</sub>	Threshold voltage	T <sub>case</sub> = 125°C		-	0.88	V
r <sub>T</sub>	On-state slope resistance	T <sub>case</sub> = 125°C		-	0.20	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source	30V, 10Ω	-	3.0	μs
		$t_r=0.5\mu s, T_j=25^\circ C$				
t <sub>q</sub>	Turn-off time	$T_j = 125^{\circ}C, V_R = 100V, dl/dt$	= 10A/µs,	-	250	μs
		$dV_{DR}/dt = 20V/\mu s$ linear to 67	7% V <sub>DRM</sub>			
Qs	Stored charge	$I_T = 2000A$ , tp = 1000us,T <sub>j</sub> = 125°C, dl/dt =10A/µs,		-	2500	μC
I <sub>RR</sub>	Reverse recovery current			-	150	А
ار	Latching current	$T_j = 25^{\circ}C,$		-	1	А
I <sub>H</sub>	Holding current	T <sub>j</sub> = 25°C,		-	200	mA

### GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	3	V
$V_{GD}$	Gate non-trigger voltage	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.3	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 40% V <sub>DRM,</sub> T <sub>case</sub> = 125°C	20	mA

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### CURVES

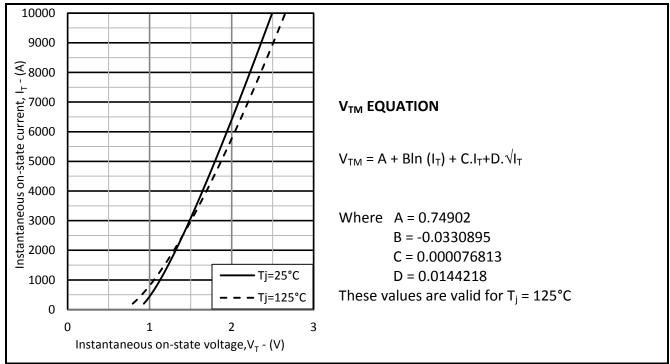


Fig.2 Maximum & minimum on-state characteristics

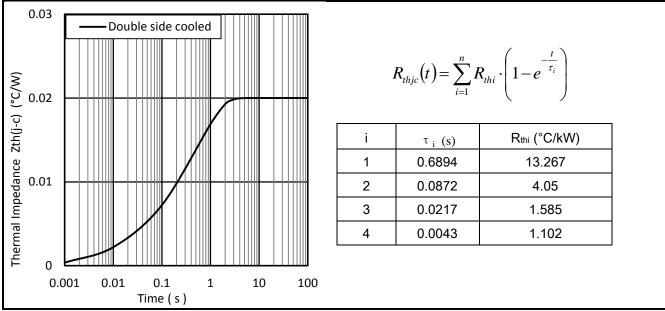
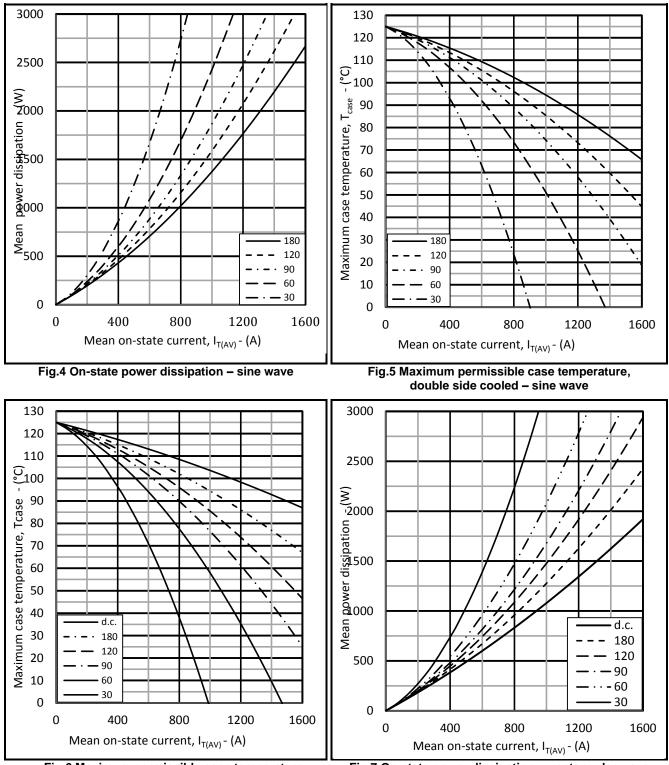
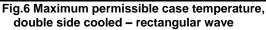


Fig.3 Maximum (limit) transient thermal impedance - junction to case (°C/W)











#### DCR1710F18

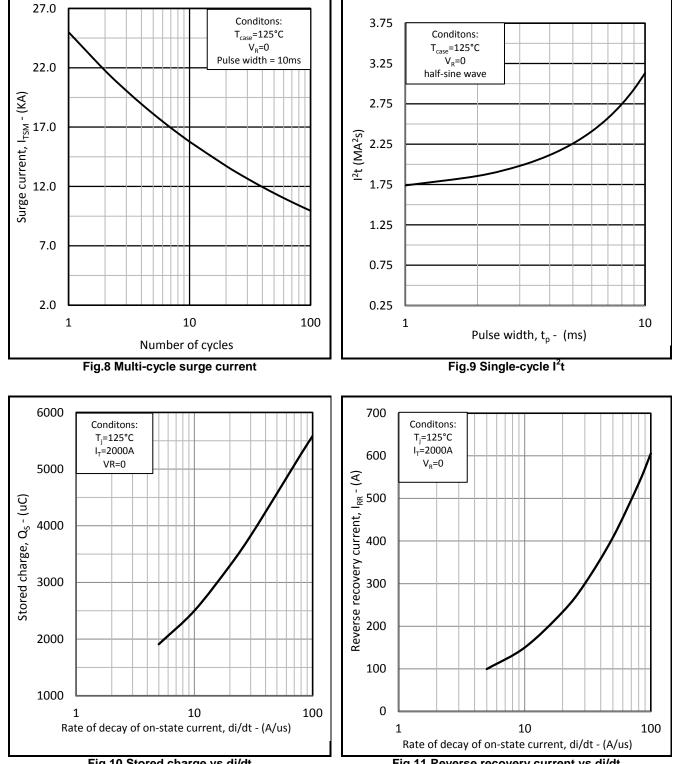


Fig.10 Stored charge vs di/dt

Fig.11 Reverse recovery current vs di/dt

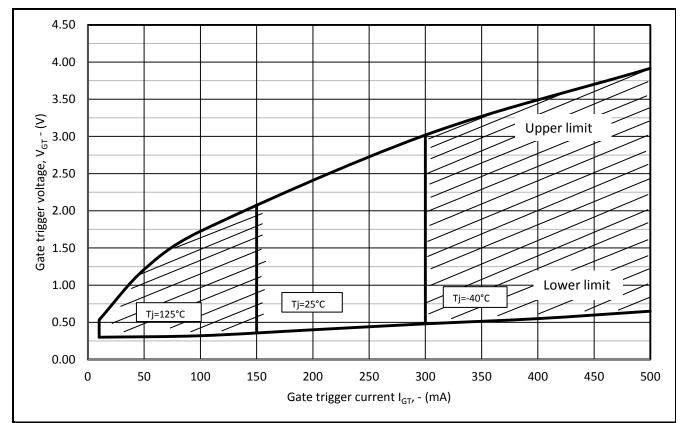


Fig.12 Gate characteristics

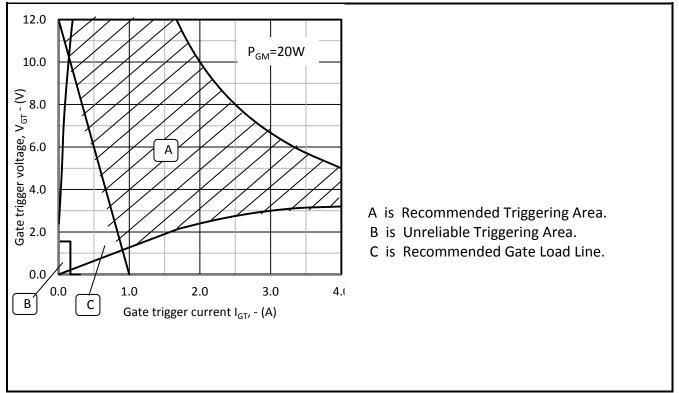


Fig.13 Gate characteristics

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### PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

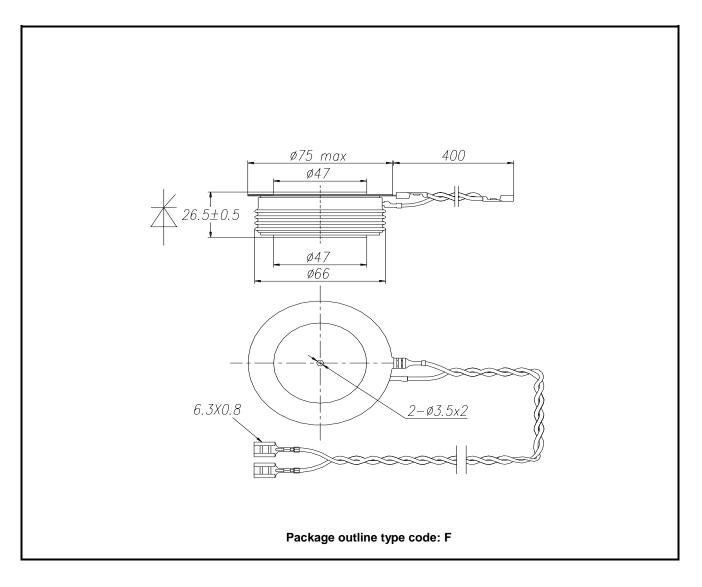


Fig.14 Package outline



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